

FORM PTO-1449	ATTY. DKT NO.	01-065-DIV	SER. NO.	0/657,061
	APPLICANT			
	AKAMATSU et al.			
FILING DATE		September 09, 2003	GROUP	28V

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
Vu	6,348,735	Feb. 19, 2002	Yamaoka		
	5,759,916	June 2, 1998	Hsu et al.		
	5,703,403	Dec. 30, 1997	Sobue et al.		
	6,066,891	May 23, 2000	Yamaoka et al.		
	4,989,064	January 29, 1991	Kubokoya et al.		
	5,345,108	Sept. 6, 1994	Kikkawa		
	4,141,022	Feb. 20, 1979	Sigg et al.		
	5,589,713	Dec. 31, 1996	Lee et al.		
	5,236,869	August 17, 1993	Takagi et al.		
	5,427,666	June 27, 1995	Mueller et al.		
	5,049,975	Sept. 17, 1991	Ajika et al.		
	5,459,353	October 17, 1995	Kanazawa		
	5,202,579	April 13, 1993	Fujii et al.		
Vu	4,887,146	Dec. 12, 1989	Hinode		

FOREIGN PATENT DOCUMENTS

TRANSLATION

	DOCUMENT NUMBER	DATE	COUNTRY	NAME	CLASS	SUB CLASS	YES	NO
Vu	B2-2555949	9/96	JAPAN				X	
	10-98041	4/98	JAPAN				X	
	10-106972	4/98	JAPAN				X	
	11-354519	12/99	JAPAN				X	
	6-275555	9/94	JAPAN				X	
	0430403	6/91	EPO					
	0525637	2/93	EPO					
	3-3395	1/91	JAPAN				X	
Vu	JP6-163877	6/94	JAPAN				X	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

EXAMINER	HUNG VU	DATE CONSIDERED	08/06/04
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FORM PTO-1449	ATTY. DKT NO.	01-065-DIV	SER. NO.	W 657,081
	APPLICANT			
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REFERENCE DESIGNATION

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
Vu	6,099,701	Aug. 2000	Liu et al.		
Vu	5,780,908	July. 1998	Sekiguchi et al.		

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TRANSLATION

	DOCUMENT NUMBER	DATE	COUNTRY	NAME	CLASS	SUB CLASS	YES	NO
Vu	5-74961	3/93	JAPAN				X	
	6-151815	5/94	JAPAN				X	
	4-42537	2/92	JAPAN				X	
	3-262127	11/91	JAPAN				X	
	63-152147	6/88	JAPAN				X	
	4-107954	4/92	JAPAN				X	
	5-90268	4/93	JAPAN				X	
Vu	63 142832	6/88	JAPAN				Abstract Only	

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Vu	Tsunohara, "EM Resistance When W Through Hole Is Used," <u>Semiconductor World</u> , Dec. 1995, pages 174-179 (partial translation provided).
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	Wendt et al., "Process Integration for Barrier Layers and Al-Alloys Using a Sputtering Cluster Tool," <u>Proceedings of the 22nd European Solid State Device Research Conference/Microelectronic Engineering</u> , Sept. 14, 1992, pages 371-374.
	Ting, "New Structure For Contact Metallurgy," <u>IBM Technical Disclosure Bulletin</u> , Vol. 25, No. 12, May 1983, pages 6398-6399.
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Vu	Koubuchi et al., Effects of Si on Electromigration of Al-Cu-Si/TiN Layered Metallization," <u>J. Vac. Sci. Technol. B</u> , Vol. 10, No. 1, Jan./Feb. 1992, pages 143-148.
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		Mandl et al., "Diffusion Barrier Properties of Ti/TiN Investigated By Transmission Electron Microscopy," <u>J. Appl. Phys.</u> , Vol. 68, No. 5, Sept. 1990, pages 2127-2132.
		Sobue et al., "Metastable Phase Formation in Al Alloy/TiN/Ti/Si Systems," <u>First International Symposium on Control of Semiconductor Interfaces</u> , Nov. 1993.
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		Gardner et al., "Mechanical Stress as a Function of Temperature for Aluminum Alloy Films," <u>J. Appl. Phys.</u> , Vol. 67, No. 4, Feb. 1990, pages 1831-1844.
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EXAMINER HUNG VU		DATE CONSIDERED 08/06/04